A new thermal low temperature ALD process for Nickel utilizing Dichlorobis(triethylphosphine)nickel(II) and 1,4-bis(trimethylgermyl)-1,4-dihydropyrazine

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Figure S1: TG curves for different cobalt precursors

Figure S2: Film uniformity as a function of distance from the inlet area

Figure S1. TG curves measured for different CoX₂(PR₃)₂ (X = Cl, Br, I; R = Me, Et) compounds.

Figure S2. Film thickness across the substrate as a function of distance from the precursor inlet area.